



EMH1307

P-Channel Power MOSFET -20V, -6.5A, 26mΩ, Single EMH8

ON Semiconductor®

<http://onsemi.com>

Features

- ON-resistance $R_{DS(on)1}$: 20mΩ(typ.)
- 1.8V drive
- Protection diode in
- Input Capacitance C_{iss} =1100pF(typ.)
- Halogen free compliance

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

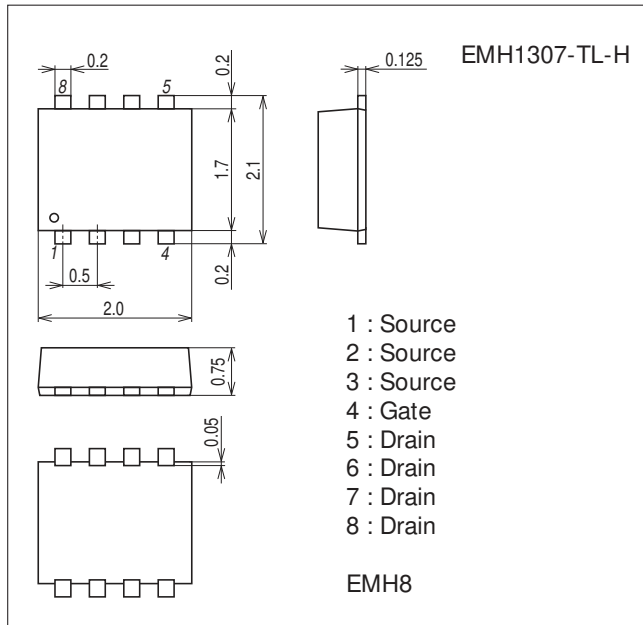
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		-20	V
Gate-to-Source Voltage	V_{GSS}		± 10	V
Drain Current (DC)	I_D		-6.5	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	-26	A
Allowable Power Dissipation	P_D	When mounted on ceramic substrate (1200mm ² ×0.8mm)	1.5	W
Channel Temperature	T_{ch}		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ)

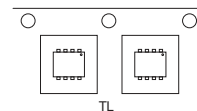
7045-001



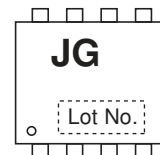
Product & Package Information

- Package : EMH8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

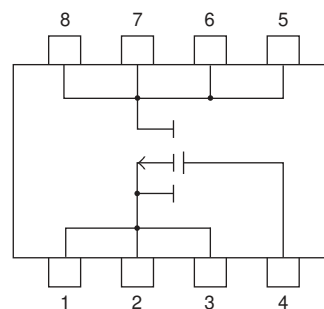
Taping Type : TL



Marking



Electrical Connection

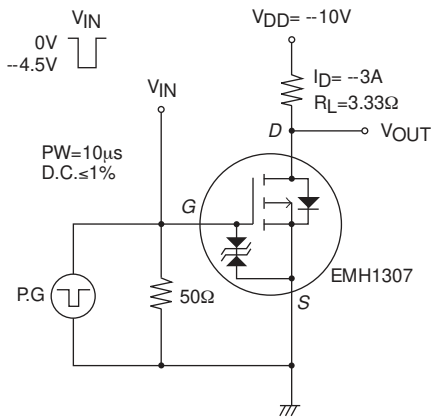


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Electrical Characteristics at Ta=25°C

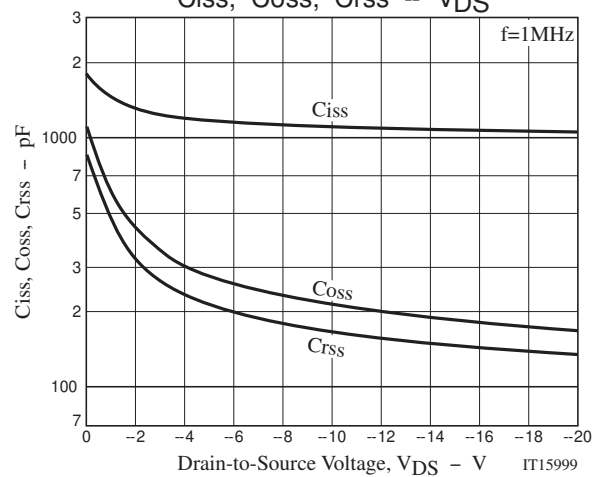
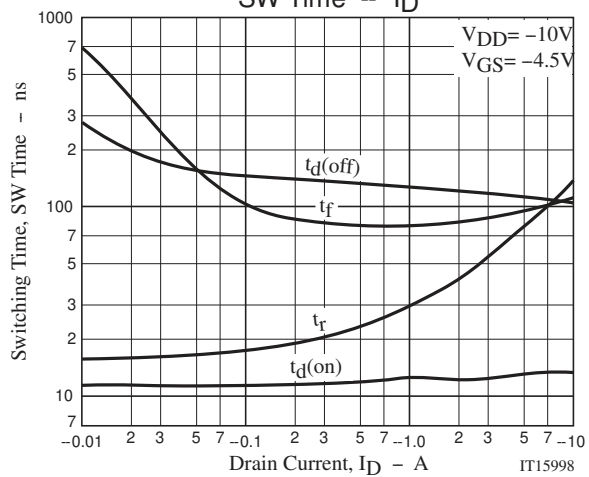
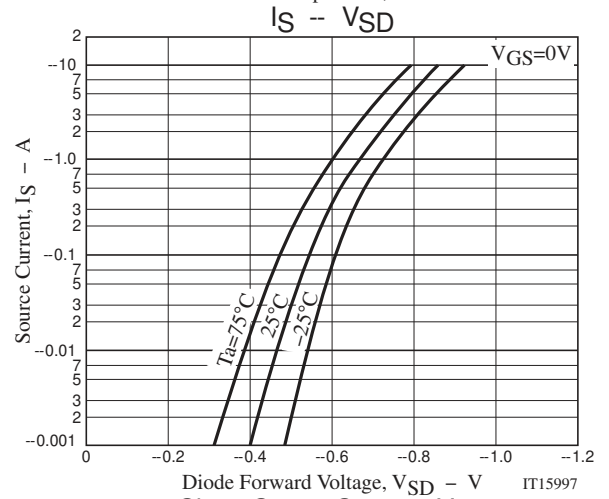
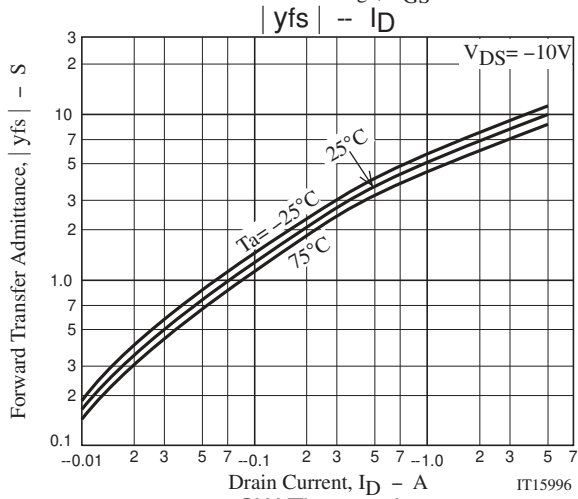
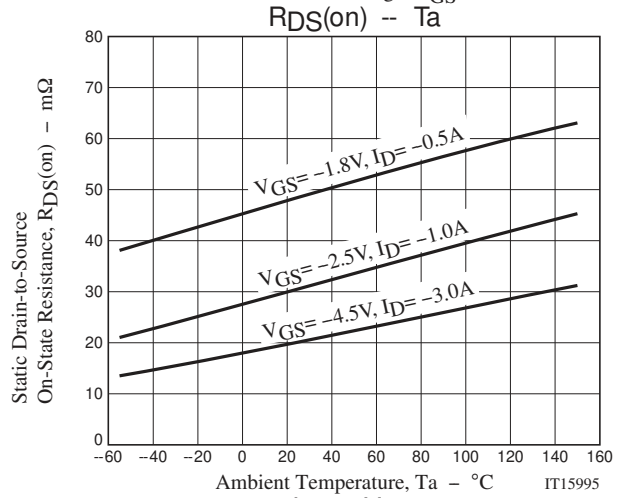
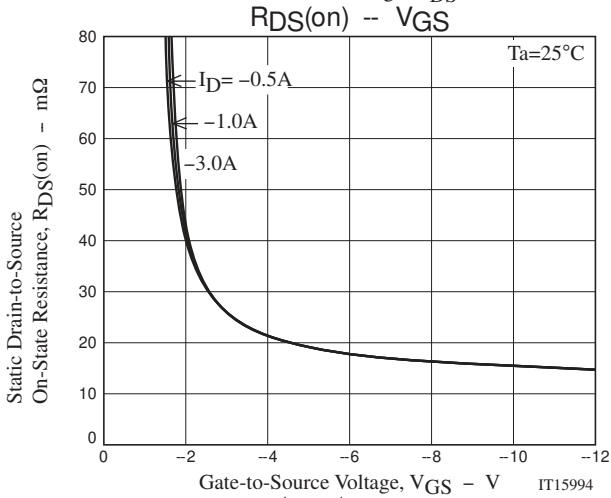
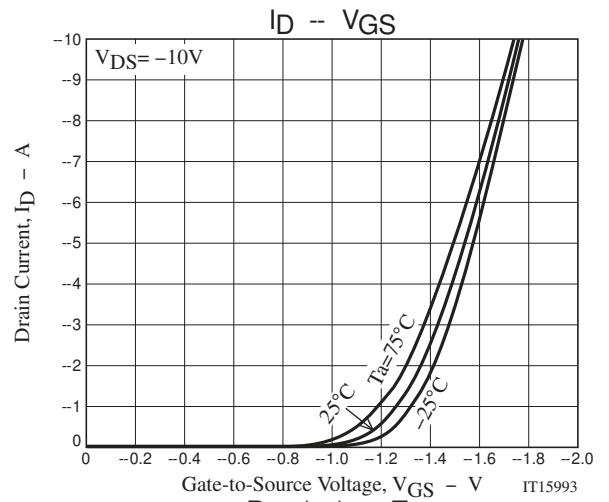
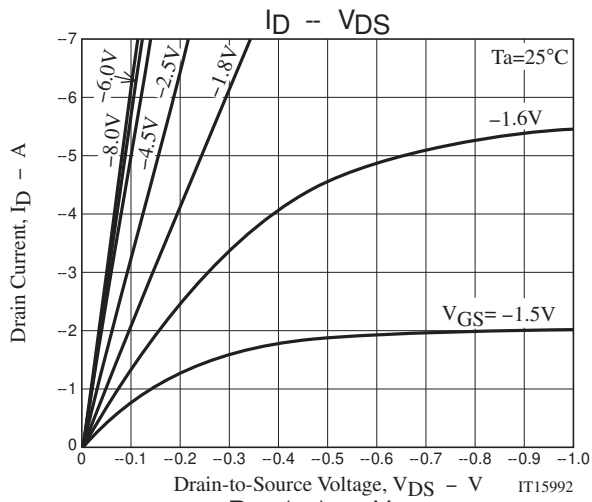
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-20			V
Zero-Gate Voltage Drain Current	IDSS	VDS=-20V, VGS=0V			-1	μA
Gate-to-Source Leakage Current	IGSS	VGS=±8V, VDS=0V			±10	μA
Cutoff Voltage	VGS(off)	VDS=-10V, ID=-1mA	-0.4		-1.3	V
Forward Transfer Admittance	yfs	VDS=-10V, ID=-3A		8.2		S
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=-3A, VGS=-4.5V		20	26	mΩ
	RDS(on)2	ID=-1.5A, VGS=-2.5V		31	44	mΩ
	RDS(on)3	ID=-0.5A, VGS=-1.8V		49	78	mΩ
Input Capacitance	Ciss	VDS=-10V, f=1MHz		1100		pF
Output Capacitance	Coss			210		pF
Reverse Transfer Capacitance	Crss			160		pF
Turn-ON Delay Time	td(on)			12.8		ns
Rise Time	tr	See specified Test Circuit.		55		ns
Turn-OFF Delay Time	td(off)			120		ns
Fall Time	tf			88		ns
Total Gate Charge	Qg			13		nC
Gate-to-Source Charge	Qgs	VDS=-10V, VGS=-4.5V, ID=-6.5A		1.9		nC
Gate-to-Drain "Miller" Charge	Qgd			3.7		nC
Diode Forward Voltage	VSD		IS=-6.5A, VGS=0V		-0.8	-1.2

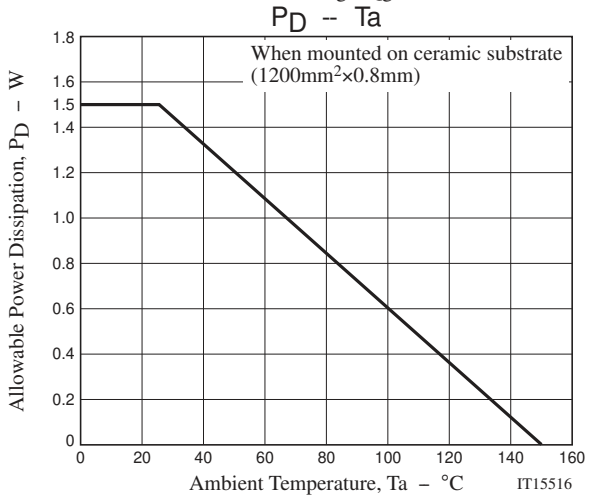
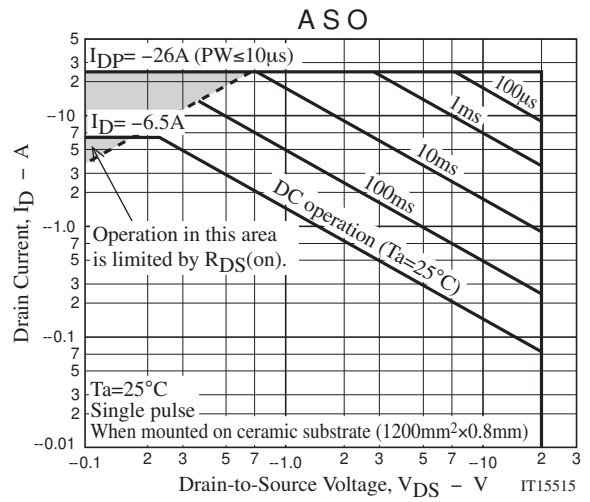
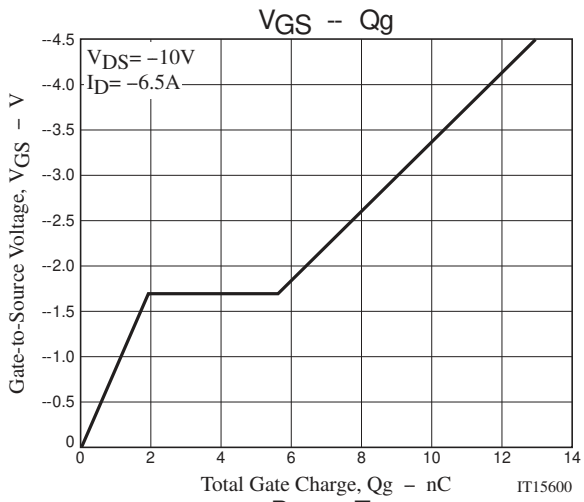
Switching Time Test Circuit



Ordering Information

Device	Package	Shipping	memo
EMH1307-TL-H	EMH8	3,000pcs./reel	Pb Free and Halogen Free





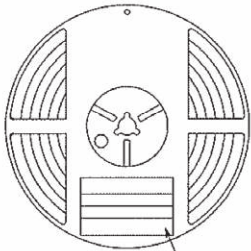
Embossed Taping Specification

EMH1307-TL-H

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
EMH8	MCP4	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

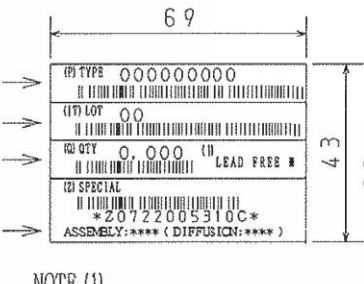
Packing method



Reel label

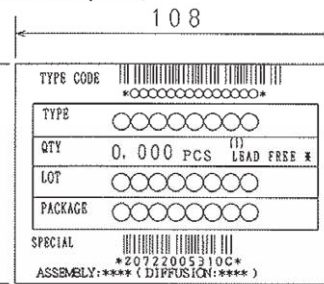
Type No. →
 LOT No. →
 Quantity →
 Origin →

Reel label, Inner box label (unit:mm)



Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



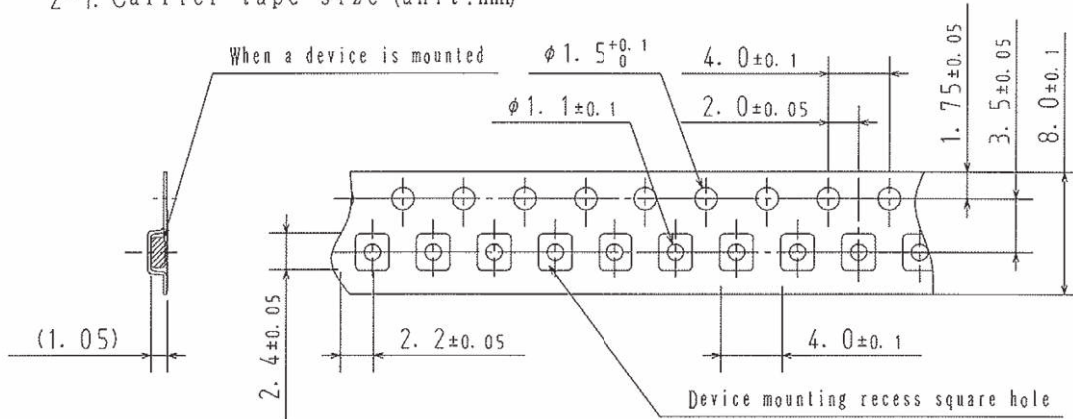
NOTE (1)

The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

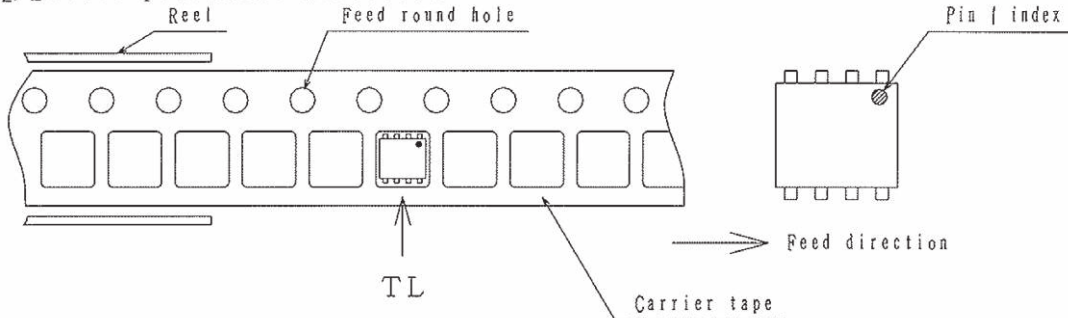
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



2-2. Device placement direction

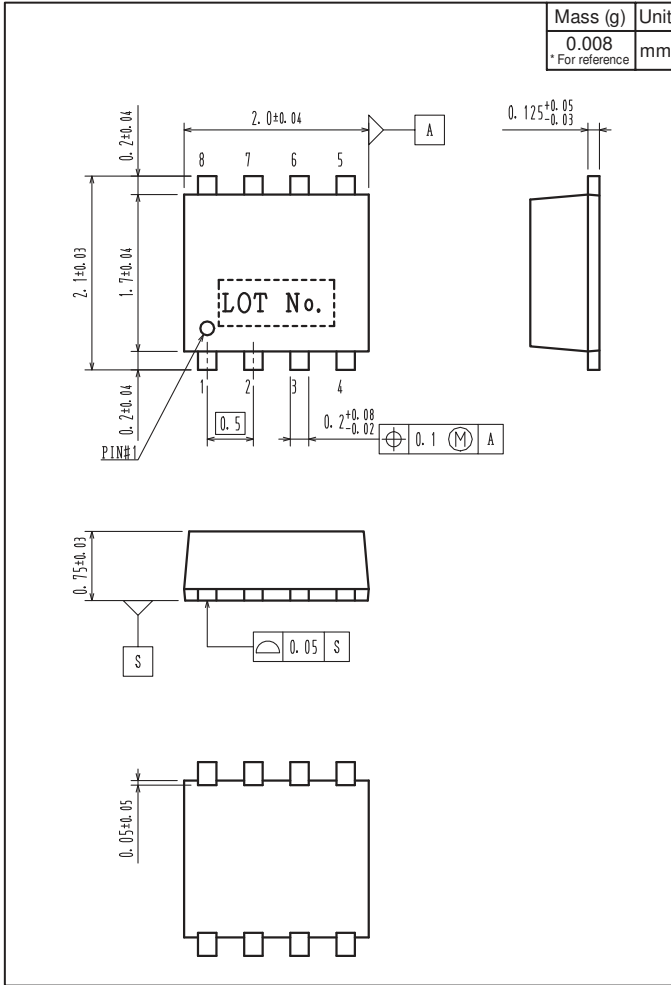


Those with pin 1 index on the feed hole side.....TL

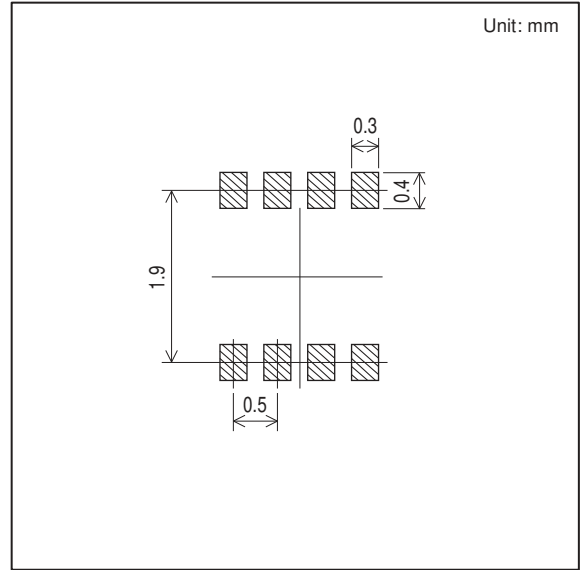
EMH1307

Outline Drawing

EMH1307-TL-H



Land Pattern Example



Note on usage : Since the EMH1307 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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